CRST085N15N, CRSS082N15N

SkyMOS1 N-MOSFET 150V, 7mΩ, 120A

Features

- Uses CRM(CQ) advanced SkyMOS1 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent Q_gx$R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Product Summary

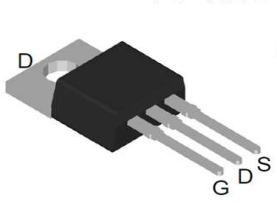
V_{DS}	150V
$R_{DS(on)}$	7mΩ
I_D	120A

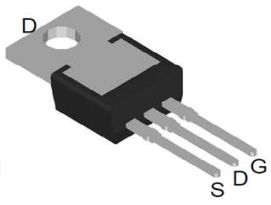
Applications

- Motor control and drive
- Battery management
- UPS (Uninterrupible Power Supplies)

100% Avalanche Tested

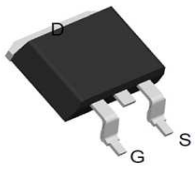
TO-220

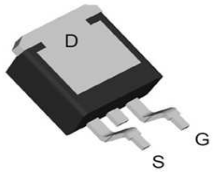




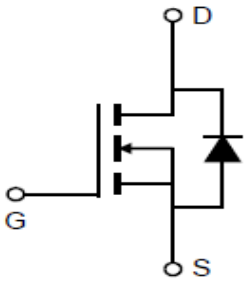
CRST085N15N

TO-263





CRSS082N15N



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRST085N15N	-	TO-220	Tube	N/A	N/A	50pcs
CRSS082N15N	-	TO-263	Tube	N/A	N/A	50pcs

Absolute Maximum Ratings

Parameter	**Symbol**	**Value**	**Unit**
Drain-source voltage	V_{DS}	150	V
Continuous drain current T_C = 25°C (Silicon limit) T_C = 25°C (Package limit) T_C = 100°C (Silicon limit)	I_D	 128 120 81	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	480	A
Avalanche Current (L=0.5mH)	I_{AS}	36	A
Avalanche energy, single pulse (L=0.5mH, Rg=25Ω)	$E_{AS(Note\ 1)}$	324	mJ
Repeative avalanche Current (L=0.5mH)	I_{AR}	16	A
Repeative avalanche (L=0.5mH)	$E_{AR(Note\ 2)}$	64	mJ
Gate-Source voltage	V_{GS}	±20	V

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Power dissipation (T_C = 25°C)	P_{tot}	227	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C

※. Notes:
1.EAS is tested at starting Tj = 25℃, L = 0.5mH, IAS = 36A, VGS = 10V.
2.Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.52	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	60	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	150	-	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	2	3	4	V	V_{DS}=V_{GS},I_D=250uA
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=150V,V_{GS}=0V T_j=25°C
		-	-	10		T_j=125°C
Gate-source leakage current	I_{GSS}	-	-	100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	7.0	8.5	mΩ	V_{GS}=10V, I_D=50A T_j=25°C TO-220
		-	6.8	8.2		TO-263
		-	11.3	14.1	mΩ	V_{GS}=10V, I_D=50A T_j=100°C TO-220
		-	11.1	13.9		TO-263
Transconductance	g_{fs}	-	91.8	-	S	V_{DS}=5V,I_D=50A
Dynamic Characteristic						
Input Capacitance	C_{iss}	-	4217	6326	pF	V_{GS}=0V, V_{DS}=75V, f=1MHz
Output Capacitance	C_{oss}	-	512	768		
Reverse Transfer Capacitance	C_{rss}	-	38	57		
Gate Total Charge	Q_G	-	63	94.5	nC	V_{GS}=10V, V_{DS}=75V, I_D=50A, f=1MHz;
Gate-Source charge	Q_{gs}	-	21	31.5		
Gate-Drain charge	Q_{gd}	-	15	22.5		
Threshold Gate Charge	$Q_{g(th)}$	-	13.5	20.3		

Turn-on delay time	$t_{d(on)}$	-	11	16.5	ns	Vds=75V Id=100A Rg=2.7Ω Vgs=10V; (Note 3,4)
Rise time	t_r	-	107	160.5		
Turn-off delay time	$t_{d(off)}$	-	54	81		
Fall time	t_f	-	102	153		
Gate resistance	R_G	-	3.0	5.5	Ω	V_{GS}=0V, V_{DS}=0V, f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.86	1.4	V	V_{GS}=0V,I_{SD}=50A
Body Diode Reverse Recovery Time	t_{rr}	-	100	200	ns	ISD=100A, VGS=0V, dIF/dt=100A/us;
Body Diode Reverse Recovery Charge	Q_{rr}	-	451	902	nC	

※. Notes
3.Pulse Test : Pulse Width ≤ 300us, duty cycle ≤ 2%.
4.Essentially independent of operating temperature.

Typical Performance Characteristics

Fig 1: Output Characteristics

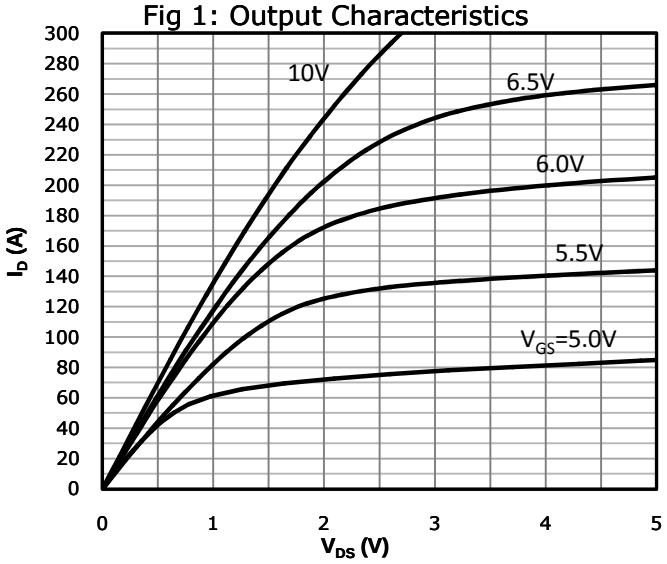


Fig 2: Transfer Characteristics

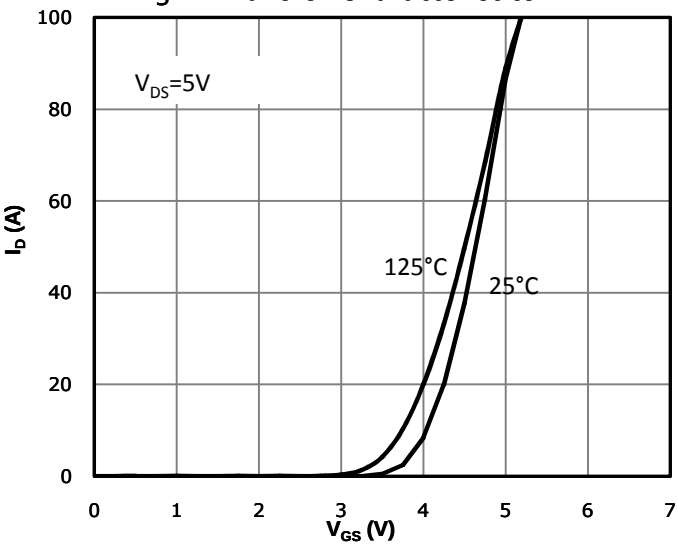


Fig 3: Rds(on) vs Drain Current and Gate Voltage

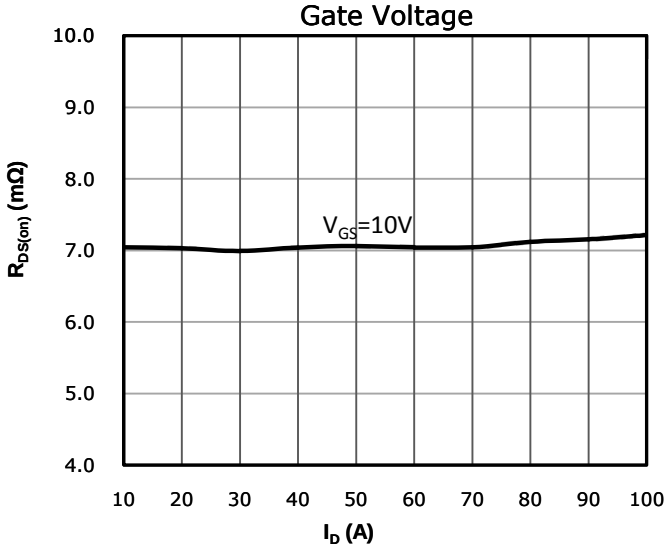


Fig 4: Rds(on) vs Gate Voltage

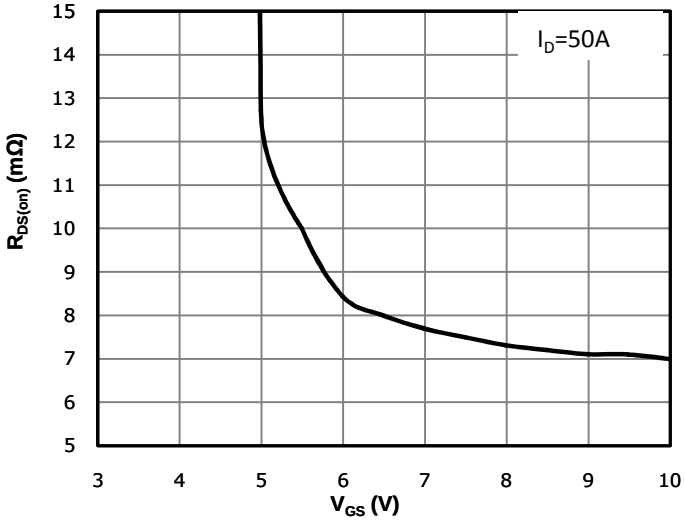


Fig 5: Rds(on) vs. Temperature

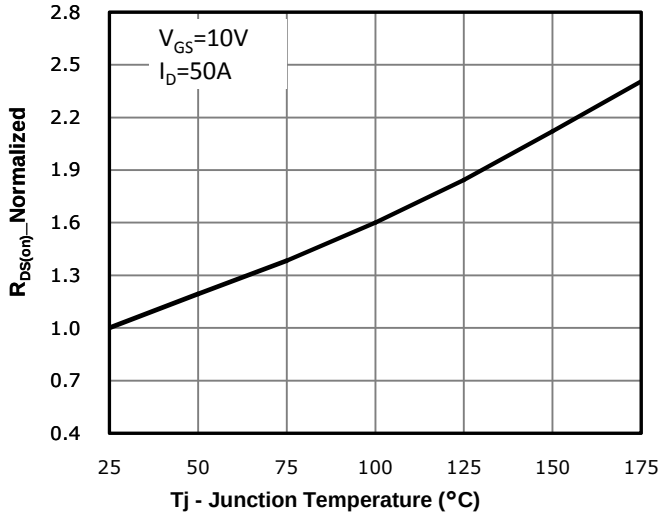


Fig 6: Capacitance Characteristics

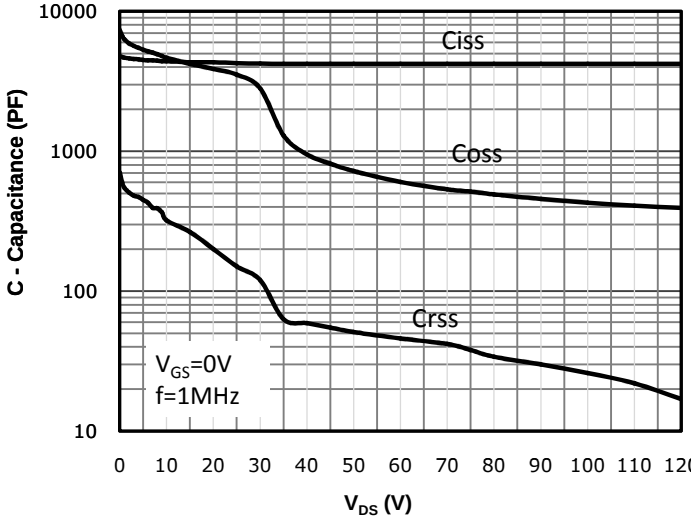


Fig 7: Gate Charge Characteristics

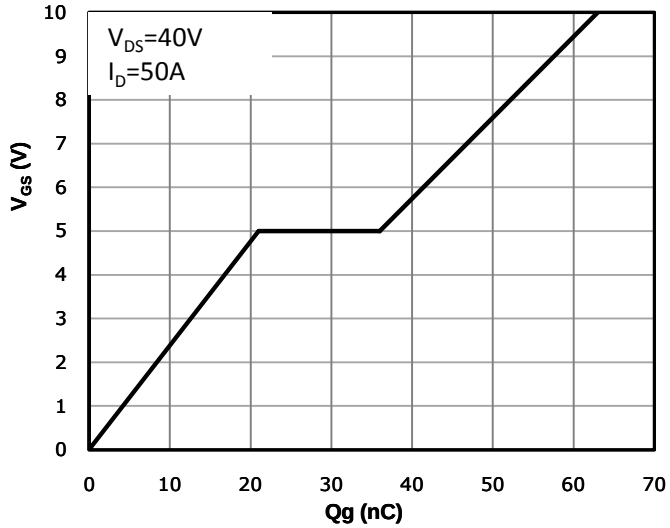


Fig 8: Body-diode Forward Characteristics

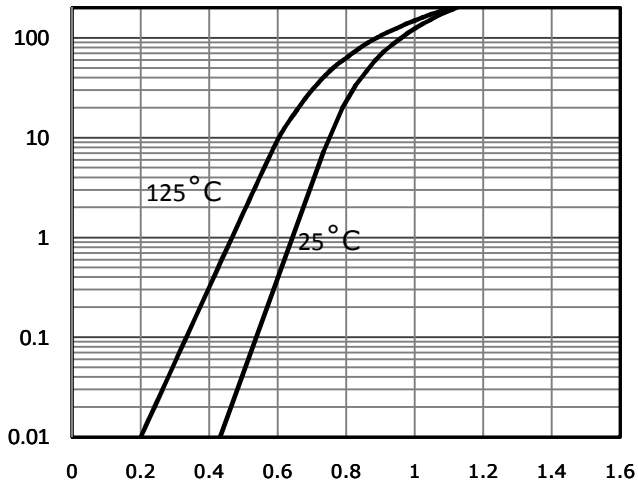


Fig 9: Power Dissipation

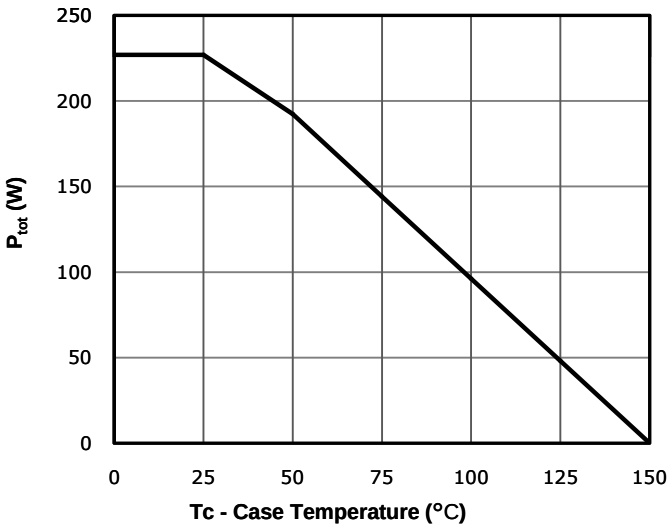


Fig 10: Drain Current Derating

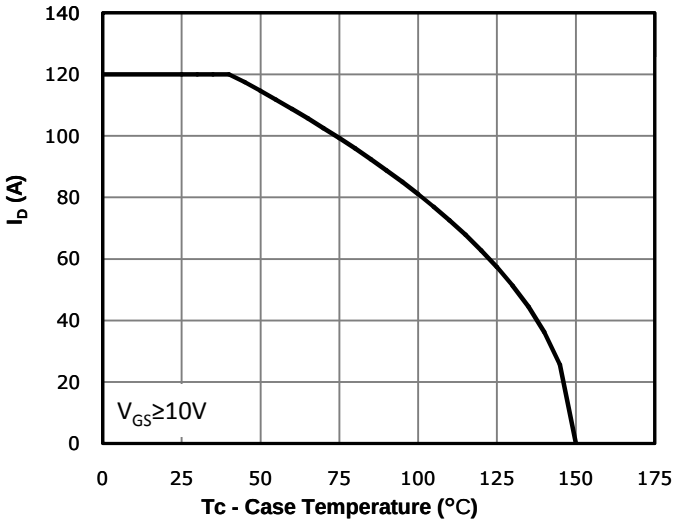


Fig 11: Safe Operating Area

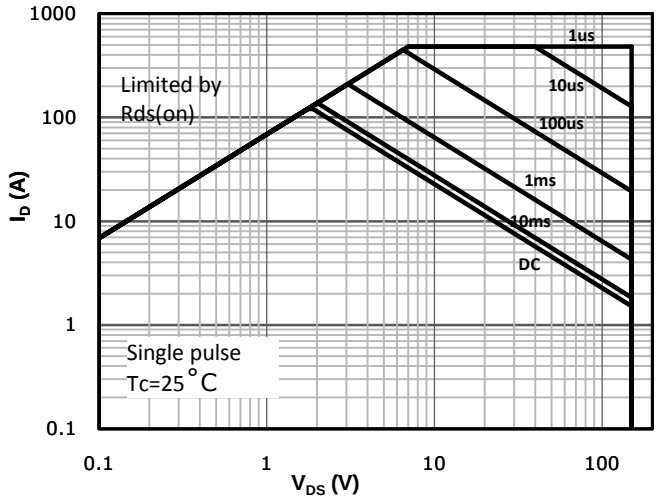
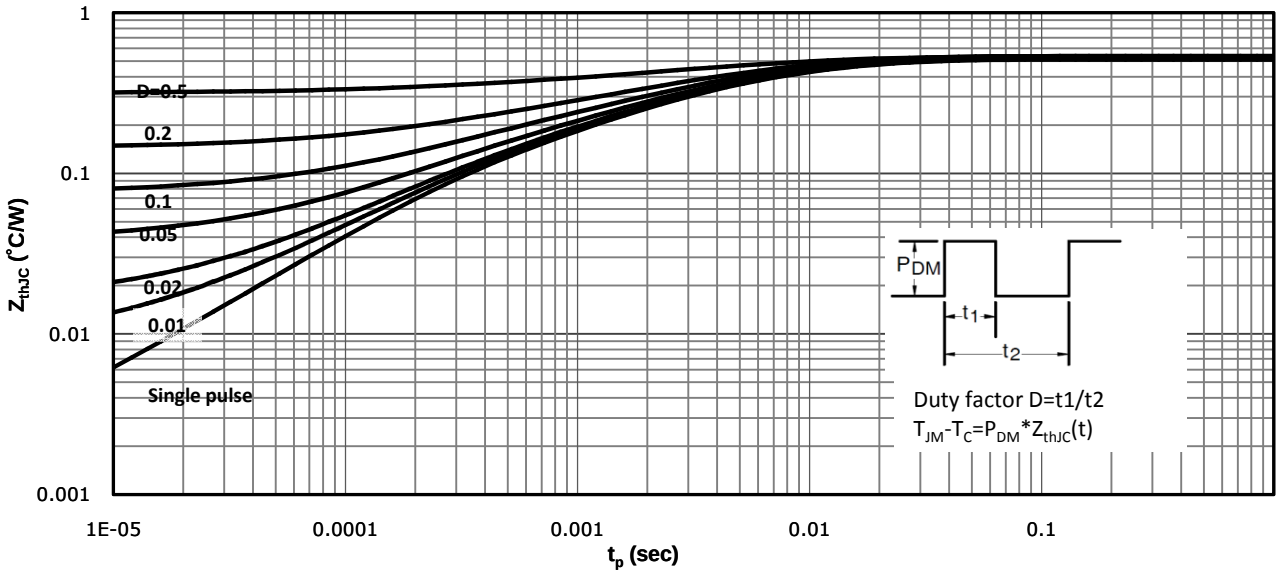
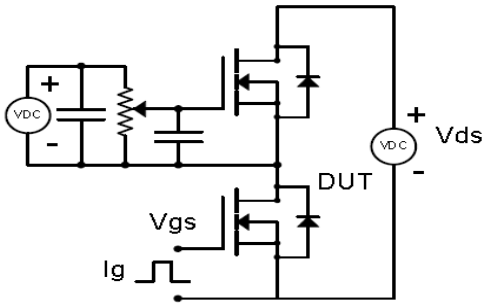


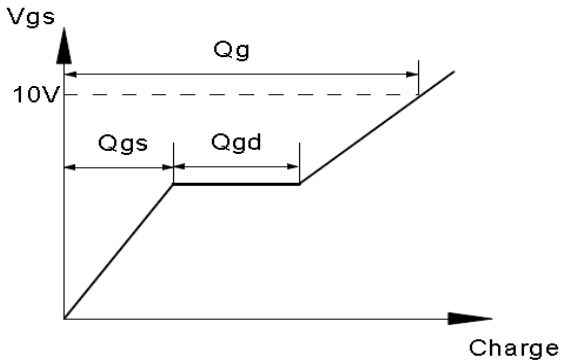
Fig 12: Max. Transient Thermal Impedance



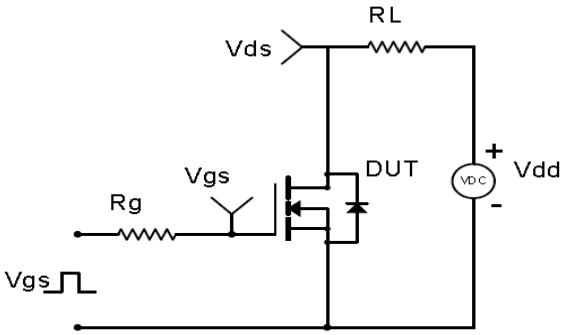
Test Circuit & Waveform

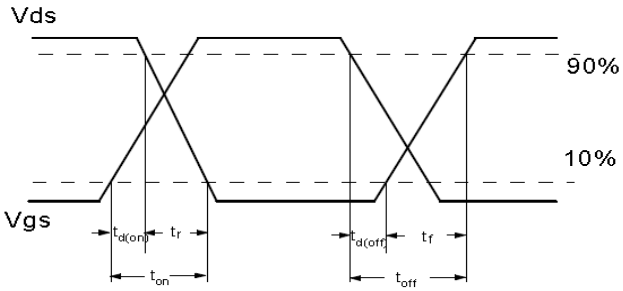
Gate Charge Test Circuit & Waveform



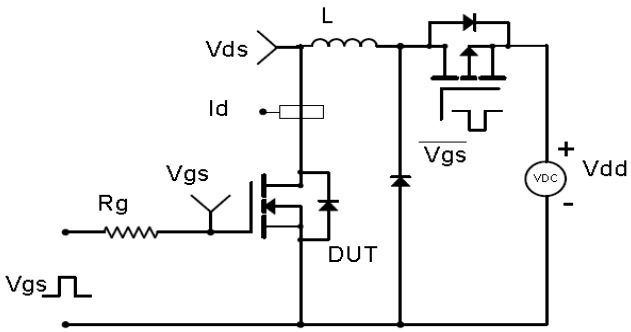


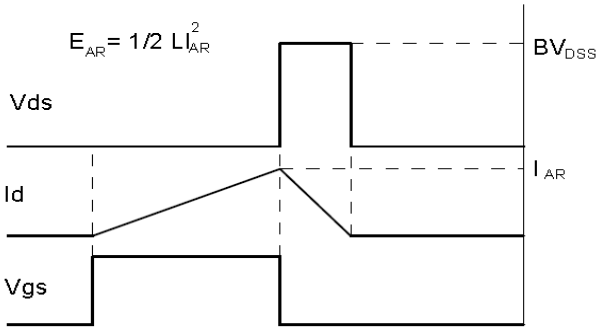
Resistive Switching Test Circuit & Waveforms



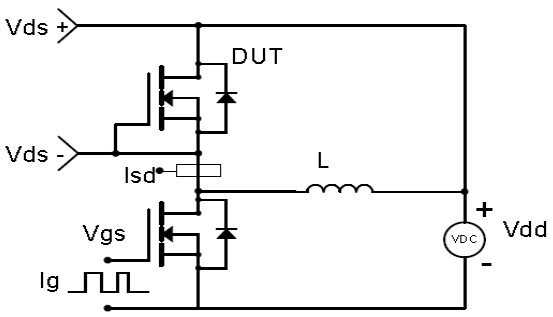


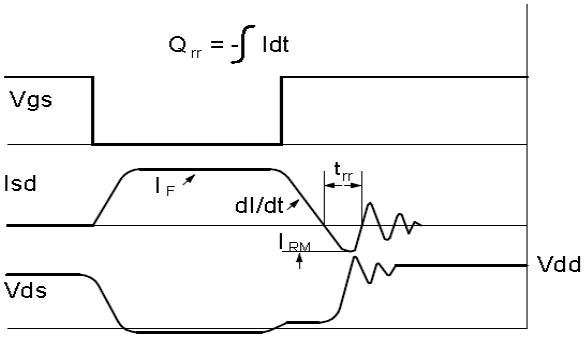
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



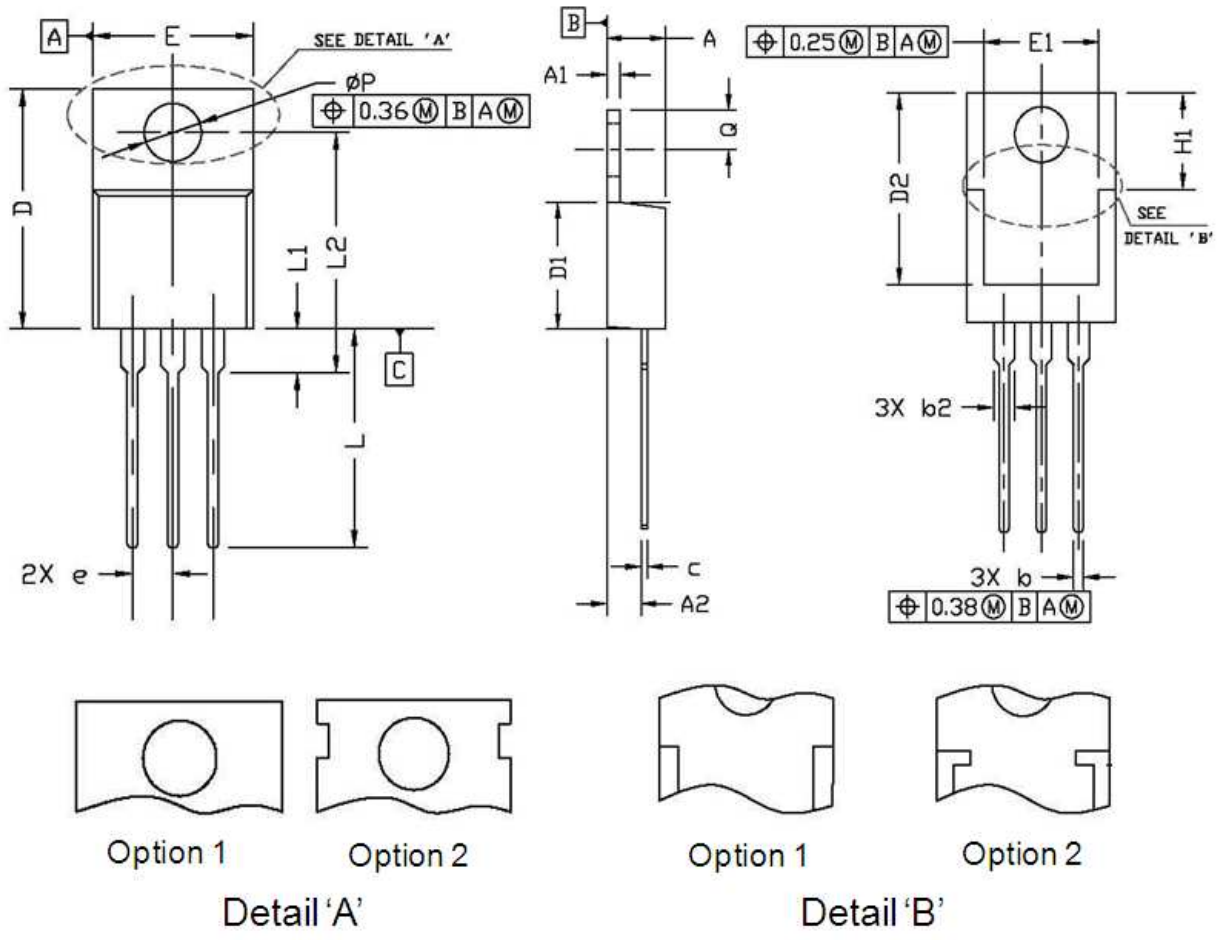


Diode Recovery Test Circuit & Waveforms





Package Outline: TO-220-3L

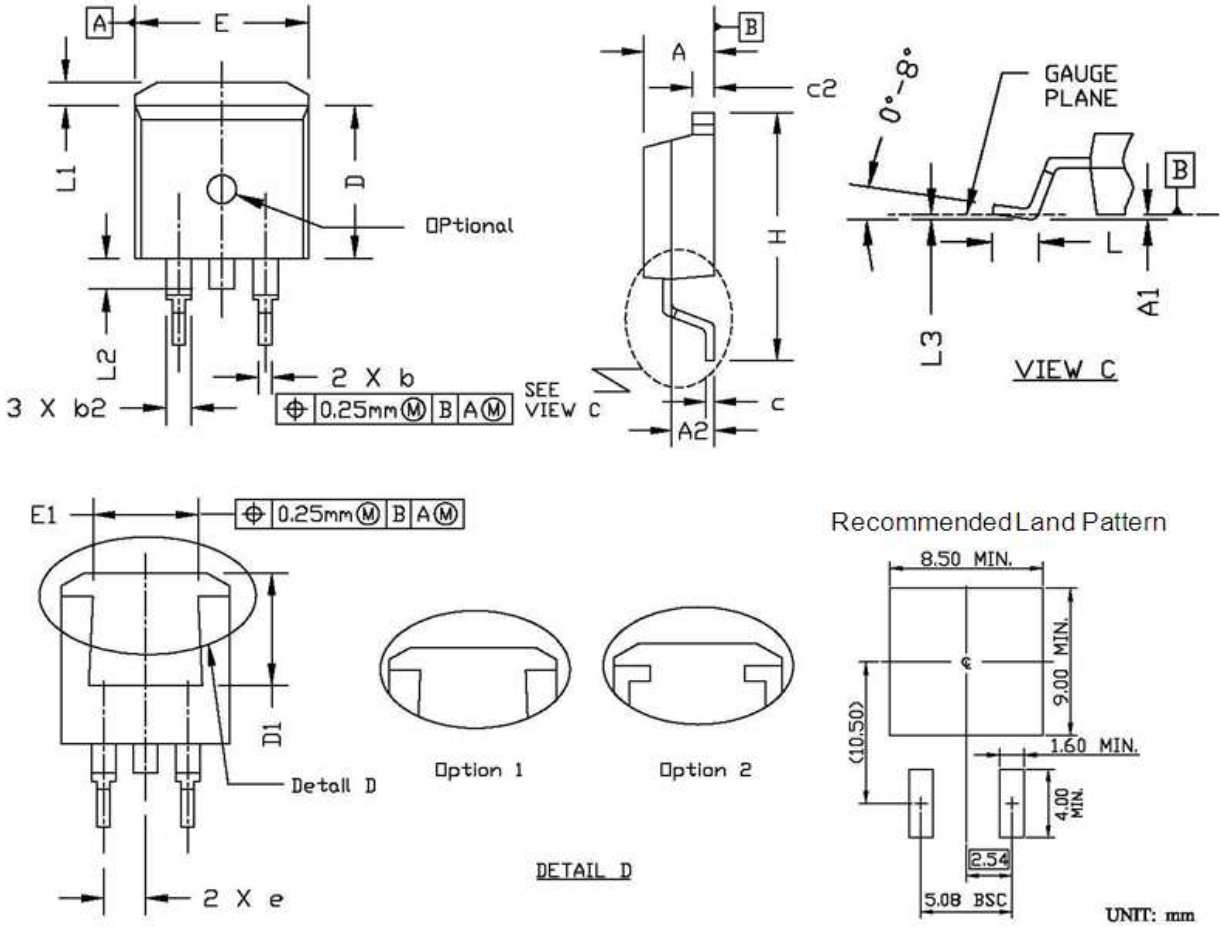


Detail 'A' Detail 'B'

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.80	0.169	0.189
A1	1.20	1.45	0.047	0.057
A2	2.20	2.90	0.087	0.114
b	0.69	0.95	0.027	0.037
b2	1.00	1.60	0.039	0.063
c	0.33	0.65	0.013	0.026
D	14.70	16.20	0.579	0.638
D1	8.59	9.65	0.338	0.380
D2	11.75	13.60	0.463	0.535
e	2.54 BSC.		0.100 BSC.	
E	9.60	10.60	0.378	0.417
E1	7.00	8.46	0.276	0.333
H1	6.20	7.00	0.244	0.276
L	12.60	14.80	0.496	0.583
L1	2.70	3.80	0.106	0.150
L2	12.13	16.50	0.478	0.650
Q	2.40	3.10	0.094	0.122
P	3.50	3.90	0.138	0.154

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Package Outline: TO-263



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.86	0.169	0.191
A1	0.00	0.25	0.000	0.010
A2	2.34	2.79	0.092	0.110
b	0.68	0.94	0.027	0.037
b2	1.15	1.35	0.045	0.053
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.38	9.45	0.330	0.372
D1	6.90	8.17	0.272	0.322
e	2.54 BSC.		0.100 BSC.	
E	9.78	10.50	0.385	0.413
E1	6.50	8.60	0.256	0.339
H	14.61	15.88	0.575	0.625
L	2.24	3.00	0.088	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
L3	0.00	0.25	0.000	0.010

Revision History

Revison	Date	Major changes
1.0	2018-11-02	Release of formal version.
1.1	2019-02-28	Revise Bug Idss Condition;
2.0	2019-05-28	Supplement package outline info&Zthjc Curve;
3.0	2020-02-20	Revise Crss Data;Add Dynamic Data Control;

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qulified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semicondutor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.